

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Accompanying Continuation Application under 37 CFR 1.53(b):

#300B
NEAR

Prior Application: Y. OKAMOTO et al
USSN 09/567,158
Filed: May 9, 2000

Group Art Unit: 1756
Examiner: N. BARRECA
For: PROCESS FOR FABRICATING SEMICONDUCTOR
INTEGRATED CIRCUIT DEVICE, AND
EXPOSING SYSTEM AND MASK INSPECTING
METHOD TO BE USED IN THE PROCESS

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

August 7, 2001

Sir:

Prior to examination, please amend the above application as follows.

IN THE CLAIMS

Please cancel claim 1 and add new claim 39 as set forth below.

39. (New) A method of making a semiconductor device, comprising the steps of:

(i) irradiating a mask, where an enlarged circuit pattern is formed, with an exposure light flux, being at least partially coherent in the ultraviolet domain; and